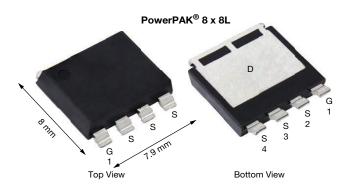
Vishay Siliconix

Automotive N-Channel 40 V (D-S) 175 °C MOSFET



PRODUCT SUMMARY					
V _{DS} (V)	40				
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.00053				
I _D (A)	701				
Configuration	Single				

FEATURES

- TrenchFET® Gen IV power MOSFET
- AEC-Q101 qualified
- 100 % R_q and UIS tested
- Thin 1.6 mm package
- · Very low thermal resistance
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



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	S

N-Channel MOSFET

ORDERING INFORMATION	
Package	PowerPAK 8 x 8L
Lead (Pb)-free and halogen-free	SQJQ140E (for detailed order number please see www.vishay.com/doc?79776)

PARAMETER		SYMBOL	LIMIT	UNIT
Drain-source voltage		V_{DS}	40	.,
Gate-source voltage		V_{GS}	± 20	V
Continuous drain current	T _C = 25 °C	1	701	А
Continuous drain current	T _C = 125 °C	- I _D	405	
Continuous source current (diode conduction)	I _S	545	
Pulsed drain current ^a		I _{DM}	1820	
Single pulse avalanche current	1 04	I _{AS}	79	I
Single pulse avalanche energy	L = 0.1 mH	E _{AS}	312	mJ
Maximum power dissipation	T _C = 25 °C	Б	600	10/
	T _C = 125 °C	P_{D}	200	W
Operating junction and storage temperature r	ange	T _J , T _{stg}	-55 to +175	00
Soldering recommendations (peak temperatu		260	°C	

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-ambient	PCB mount b	R_{thJA}	44	°C/W
Junction-to-case (drain)		R_{thJC}	0.25	C/VV

Notes

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %
- b. When mounted on 1" square PCB (FR4 material)
- c. See solder profile (www.vishay.com/doc?73257). The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection



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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static	•			l	•			
Drain-source breakdown voltage	V_{DS}	$V_{GS} = 0$, $I_D = 250 \mu A$		40	-	-	V	
Gate-source threshold voltage	V _{GS(th)}	V _{DS} =	- V _{GS} , I _D = 250 μA	2.3	2.7	3.3	V	
Gate-source leakage	I _{GSS}	V _{DS} =	0 V, V _{GS} = ± 20 V	-	-	± 100	nA	
		$V_{GS} = 0 V$	V _{DS} = 40 V	-	-	1		
Zero gate voltage drain current	I _{DSS}	V _{GS} = 0 V	V _{DS} = 40 V, T _J = 125 °C	-	-	50	μΑ	
		V _{GS} = 0 V	V _{DS} = 40 V, T _J = 175 °C	-	-	150	1	
On-state drain current a	I _{D(on)}	V _{GS} = 10 V	V _{DS} ≥ 5 V	100	-	-	Α	
		V _{GS} = 10 V	I _D = 20 A	-	0.00044	0.00053	Ω	
Drain-source on-state resistance ^a	R _{DS(on)}	V _{GS} = 10 V	I _D = 20 A, T _J = 125 °C	-	-	0.00092		
		V _{GS} = 10 V	I _D = 20 A, T _J = 175 °C	-	-	0.0013		
Forward transconductance b	9 _{fs}	V _{DS} = 15 V, I _D = 80 A		-	160	-	S	
Dynamic ^b								
Input capacitance	C _{iss}			-	12 140	17 000		
Output capacitance	C _{oss}	$V_{GS} = 0 V$	$V_{DS} = 25 \text{ V}, f = 1 \text{ MHz}$	-	4740	6636	pF	
Reverse transfer capacitance	C _{rss}			-	308	432		
Total gate charge ^c	Q_g			-	192	288		
Gate-source charge c	Q_{gs}	V _{GS} = 10 V	$V_{GS} = 10 \text{ V}$ $V_{DS} = 20 \text{ V}, I_D = 40 \text{ A}$		55	-	nC	
Gate-drain charge ^c	Q_{gd}			-	41	-		
Gate resistance	R_g		f = 1 MHz	0.8	1.6	2.4	Ω	
Turn-on delay time ^c	t _{d(on)}			-	26	39		
Rise time ^c	t _r	$V_{DD} = 20 \text{ V}, \text{ R}_{L} = 0.5 \Omega$ $I_{D} \cong 40 \text{ A}, \text{ V}_{GEN} = 10 \text{ V}, \text{ R}_{g} = 1 \Omega$		-	78	117	ns	
Turn-off delay time ^c	t _{d(off)}			-	62	93		
Fall time ^c	t _f			-	32	48		
Source-Drain Diode Ratings and Char	racteristics b							
Reverse recovery time	t _{rr}	V _{DD} = 32 V, I _{FM} = 20 A, di/dt = 100 A/µs		-	94	188	ns	
Reverse recovery charge	Q_{rr}			-	177	354	nC	
Reverse recovery current	I _{RM}			-	-3.2	-	Α	
Pulsed current a	I _{SM}			-	-	1600	Α	
. 4.004 04.101.1	- OIVI							

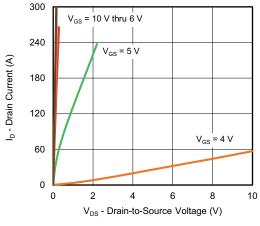
Notes

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %
- b. Guaranteed by design, not subject to production testing
- c. Independent of operating temperature

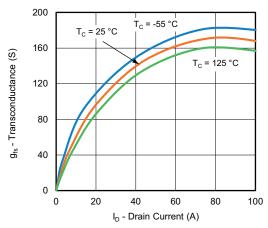
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



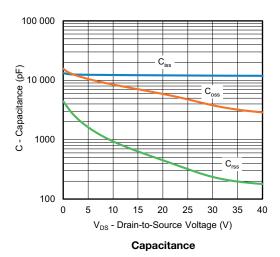
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

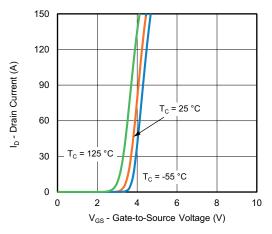


Output Characteristics

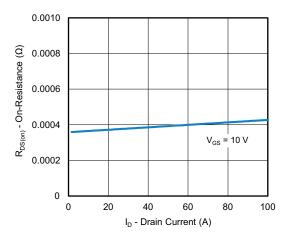


Transconductance

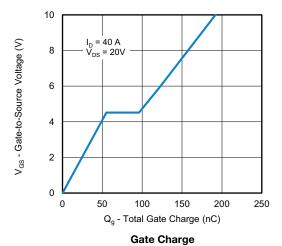




Transfer Characteristics

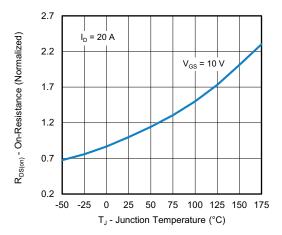


On-Resistance vs. Drain Current

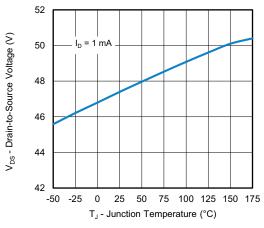




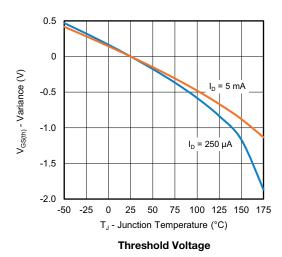
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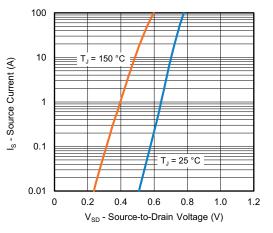


On-Resistance vs. Junction Temperature

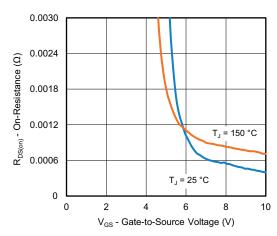


Drain Source Breakdown vs. Junction Temperature

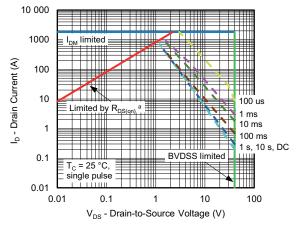




Source Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage



Safe Operating Area

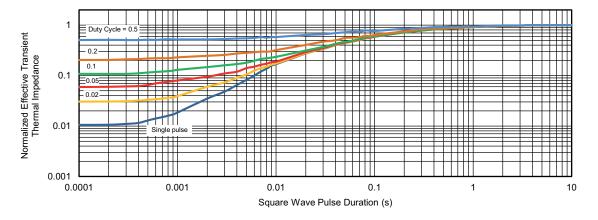
Note

a. V_{GS} > minimum V_{GS} at which R_{DS(on)} is specified

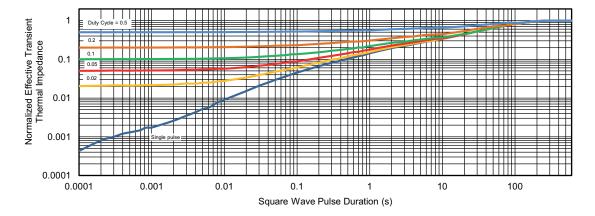
For technical questions, contact: automostech



THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



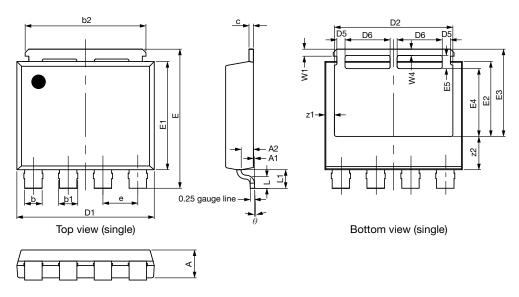
Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see www.vishay.com/ppg?79764.



www.vishay.com

PowerPAK® 8 x 8L BWL Case Outline 2



DIM.		MILLIMETERS INCHE			INCHES	S		
DIM.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.		
Α	1.50	1.60	1.70	0.059	0.063	0.067		
A1	0.00	-	0.127	0.000	-	0.005		
A2	0.655	0.705	0.755	0.026	0.028	0.030		
b	0.92	1.00	1.08	0.036	0.039	0.043		
b1	1.02	1.10	1.18	0.040	0.043	0.046		
b2	6.84	6.94	7.04	0.269	0.273	0.277		
С	0.20	0.25	0.30	0.008	0.010	0.012		
D1	7.80	7.90	8.00	0.307	0.311	0.315		
D2	6.70	6.80	6.90	0.264	0.268	0.272		
D5	0.37	0.47	0.57	0.015	0.019	0.022		
D6	2.49	2.59	2.69	0.098	0.102	0.106		
е	1.97	2.00	2.03	0.078	0.079	0.080		
Е	7.90	8.00	8.10	0.311	0.315	0.319		
E1	6.12	6.22	6.32	0.241	0.245	0.249		
E2	4.21	4.31	4.41	0.166	0.170	0.174		
E3	4.92	5.02	5.12	0.194	0.198	0.202		
E4	3.80	3.90	4.00	0.150	0.154	0.157		
E5	0.65	0.75	0.85	0.026	0.030	0.033		
L	0.61	0.68	0.75	0.024	0.027	0.030		
L1	1.00	1.07	1.15	0.039	0.042	0.045		
W1	0.30	0.40	0.50	0.012	0.016	0.020		
W4	0.32	0.37	0.42	0.013	0.015	0.017		
z1	0.45	0.55	0.65	0.018	0.022	0.026		
z2	1.81	1.91	2.01	0.071	0.075	0.079		
θ	0°	-	5°	0°	-	5°		

ECN: S19-0643-Rev. B, 05-Aug-2019

Note

DWG: 6073

• Millimeter will govern

Revison: 05-Aug-2019 1 Document Number: 79736



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